RDIMM	UDIMM	SODIMM	mini DIMM
OWNITE COLUMN		and Storage systems and providing superior cost an has started to relinquish it industry's mainstream tec	market segments from oks to Printers, Networking many more for several year id performance criteria. DDR is role as the memory hnology to DDR3 and is iggacy product by early 2011

DDR2 - 240-Pin DIMM - Registered ECC

Standard Profile (1.181") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
100	WD2RE01GX809-xxxx-yyz	1 rank	128x72	128Mx8	1.8V
1GB	WD2RE01GX418-xxxx-yyz	1 rank	128x72	128Mx4	1.8V
2GB	WD2RE02GX818-xxxx-yyz	2 rank	256x72	128Mx8	1.8V
-	WD2RE04GX418-xxxx-yyz	1 rank	512x72	512Mx4	1.8V
4GB	WD2RE04GX436-xxxx-yyz	2 rank	512x72	256Mx4	1.8V
-	WD2RE04GX836-xxxx-yyz	4 rank	512x72	128Mx8	1.8V
8GB -	WD2RE08GX436-xxxx-yyz	2 rank	1024x72	512Mx4	1.8V
	WD2RE08GX836-xxxx-yyz	4 rank	1024x72	256Mx8	1.8V

Very Low Profile (0.72") with Nominal Voltage (1.8V)

Density	Part Number	Rank	DIMM Config	Component Config	Voltage
1GB	WD2RE01GX809V-xxxx-yyz	1 rank	128x72	128Mx8	1.8V
IGB	WD2RE01GX418V-xxxx-yyz	1 rank	128x72	128Mx4	1.8V
2GB	WD2RE02GX818V-xxxx-yyz	2 rank	256x72	128Mx8	1.8V
100	WD2RE04GX418V-xxxx-yyz	1 rank	512x72	512Mx4	1.8V
4GB	WD2RE04GX818V-xxxx-yyz	2 rank	512x72	256Mx8	1.8V
8GB	WD2RE08GX818V-xxxxx-yyz	2 rank	1024x72	512Mx8	1.8V

 $(xxxxx)\;$ Modules Speed (MHz) and CAS Latency

8001: 800MHz CL6
800G : 800MHz CL5
667G : 667MHz CL5
533E : 533MHz CL4

	000E . 000MINZ 0E4	
	DRAM Manufacturer a	and Die Revision
(yy) =	P: Samsung	A: A-Die
	H: Micron	B: B-Die
	C: Hynix	C: C-Die

Buffer / Register set (Only applies to Registered/Buffered modules)

(z) = I: Inphi

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D: IDT L: Intel